UNITED STATES SECURITIES AND EXCHANGE COMMISSION

Washington, D.C. 20549

FORM 8-K

CURRENT REPORT
Pursuant to Section 13 or 15(d)
of The Securities Exchange Act of 1934

March 14, 2017

Date of Report (Date of earliest event reported)

DIODES INCORPORATED

(Exact name of registrant as specified in its charter)

Delaware (State or other jurisdiction of incorporation) 002-25577 (Commission File Number) 95-2039518 (IRS Employer Identification No.)

4949 Hedgcoxe Road, Suite 200 Plano, Texas (Address of principal executive offices)

75024 (Zip Code)

(972) 987-3900 (Registrant's telephone number, including area code)

Chec	ck the appropriate box below if the Form 8-K filing is intended to simultaneously satisfy the filing obligation of the registrant under any of the following
	isions:
	Written communications pursuant to Rule 425 under the Securities Act (17 CFR 230.425)
	Soliciting material pursuant to Rule 14a-12 under the Exchange Act (17 CFR 240.14a-12)
	Pre-commencement communications pursuant to Rule 14d-2(b) under the Exchange Act (17 CFR 240.14d-2(b))
	Pre-commencement communications pursuant to Rule 13e-4(c) under the Exchange Act (17 CFR 240.13e-4(c))

Item 8.01 Other Events.

Members of the management of Diodes Incorporated (the "Company") will present at the 29th Annual ROTH Conference on March 14, 2017. A copy of the corporate presentation slides are attached hereto as Exhibit 99.1 and are incorporated by reference herein. The webcast and archived replay of the Company's presentation may be accessed in the Investor Relations section of the Company's website at www.diodes.com

Item 9.01 Financial Statements and Exhibits.

(d) Exhibits.

Exhibit

Number Description

99.1 Corporate Presentation Slides

SIGNATURES

Pursuant to the requirements of the Securities Exchange Act of 1934, the Registrant has duly caused this report to be signed on its behalf by the undersigned hereunto duly authorized.

Dated: March 14, 2017 DIODES INCORPORATED

By /s/ Richard D. White RICHARD D. WHITE Chief Financial Officer

Index to Exhibits

Exhibit

Number Description

99.1 Corporate Presentation Slides



Investor Relations Presentation

Plano, Texas March 14, 2017

Safe Harbor Statement

Any statements set forth herein that are not historical facts are forward-looking statements that involve risks and uncertainties that could cause actual results to differ materially from those in the forward-looking statements. Such forward-looking statements include, but are not limited to, statements regarding updates to Diodes Incorporated's first quarter 2017 business outlook as of March 14, 2017, which include the following: expect revenue to range between \$220 million and \$240 million, or down 5.2 to up 3.4 percent sequentially, reflecting typical seasonality as well as a one-month impact from the KFAB fire; expect GAAP and non-GAAP gross margin to be 28.5 percent, plus or minus 1 percent; non-GAAP operating expenses, which are GAAP operating expense adjusted for retention costs and amortization of acquisition-related intangible assets, are expected to be approximately 25.0 percent of revenue, plus or minus 1 percent; expect other expense to be approximately 4.3 million, which includes 1.5 million of KFAB cleanup and repair costs; expect income tax rate to be 29 percent, plus or minus 3 percent, and shares used to calculate diluted EPS for the first quarter are anticipated to be approximately 50.4 million; purchase accounting adjustments for Pericom and previous acquisitions of \$4.2 million after tax are not included in these non-GAAP estimates; KFAB facility will cease operations late in third quarter 2017 with production moved to other Diodes' wafer fabs and external foundries and the premises vacated by November 15, 2017; pre-tax closure costs related to KFAB are expected to be \$10 million to \$12 million in 2017 with approximately \$1.1 million in first quarter 2017; and other statements identified by words such as "estimates," "expects," "projects," "plans," "will" and similar expressions.

Potential risks and uncertainties include, but are not limited to, such factors as the risk that such expectations may not be met, the risk that the expected benefits of acquisitions may not be realized. Diodes business and growth strategy, the introduction and market reception to new product announcements; fluctuations in product demand and supply; prospects for the global economy; continued introduction of new products; Diodes' ability to maintain customer and vendor relationships; technological advancements; impact of competitive products and pricing; growth in targeted markets; successfully make additional acquisitions; risks of domestic and foreign operations, including excessive operation costs, labor shortages, higher tax rates and joint venture prospects; unfavorable currency exchange rates; availability of tax credits; Diodes' ability to maintain its current growth strategy or continue to maintain its current performance and loadings in manufacturing facilities; our future guidance may be incorrect; the global economic weakness may be more severe or last longer than Diodes currently anticipate; breaches of our information technology systems; and other information, including the "Risk Factors," detailed from time to time in filings with the United States Securities and Exchange Commission.

This presentation also contains non-GAAP measures. See the Company's press release on February 14, 2017 titled, "Diodes Incorporated Reports Fourth Quarter and Fiscal 2016 Financial Results" for detailed information related to the Company's non-GAAP measures and a reconciliation of GAAP net income to non-GAAP net income.

Management Representative



Dr. Keh-Shew Lu President and CEO

Diodes Incorporated Since 2005
Texas Instruments 27 years

Experience:

- Senior Vice President of TI Worldwide Analog and Logic
- President of Texas Instruments Asia

Education:

- Master's Degree and Doctorate in Electrical Engineering Texas Tech University
- Bachelor's Degree in Engineering National Cheng Kung University - Taiwan



Company Representative

Laura Mehrl

Director of Investor Relations

Since May 2010

Experience:

- Director of Investor Relations, Diodes Incorporated, Plano, Texas
- Senior Business Development Manager, STMicroelectronics, Carrollton, Texas
- Sales Director for Analog Devices Inc., Shanghai, China
- Product Marketing Manager at Texas Instruments (TI), Dallas, Texas
- Senior Engineer at Lattice Semiconductor Inc., Hillsboro, Oregon
- Wafer fab design engineer and product engineer at TI, Lubbock, Texas

Education:

- MBA with concentration in International Marketing, Texas Tech University
- BS in Electrical and Computer Engineering, University of Iowa



About Diodes Incorporated

A leading global manufacturer and supplier of high-quality application specific, standard products within the broad discrete, logic and analog markets, serving the consumer, computing, communications, Industrial and automotive segments.





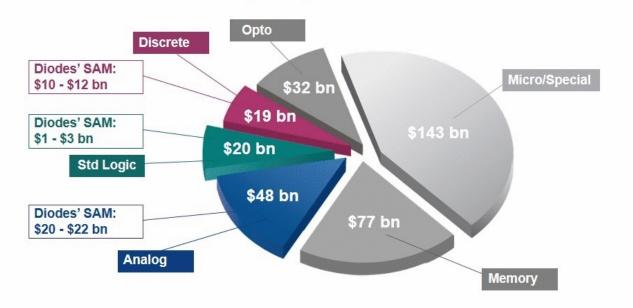
Business Objective

To consistently achieve above-market profitable growth, utilizing our innovative and cost-effective packaging and silicon technology, suited for high volume, high growth markets by leveraging process expertise and design excellence to deliver high quality semiconductor products.



Significant Market Opportunity

2016 Total Semiconductor Market (\$339 bn)

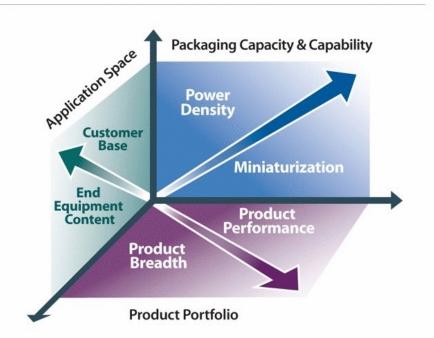




Diodes Growth Strategy

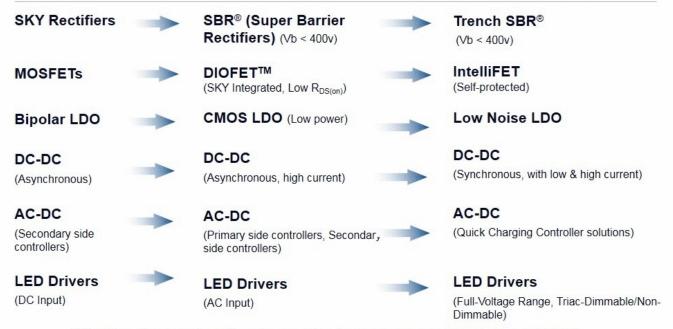
Many Paths for Growth:

- Product Portfolio
 - Product arena
 - Product line expansion
 - Performance enhancement
- Application Space
 - Targeted end equipment
 - Broad customer base
 - Increased product coverage
- Packaging Breadth
 - Broad packaging portfolio
 - Increased power density
 - Small form factor





Performance Enhancement



Diodes' product upgrade has expanded our SAM.



Efficiency, Functionality and Control for Smartphones

LED Backlighting

LED Drivers **Boost Converters** Schottky Diodes

LED Flash Module

Camera Flash Drivers ZXMN series MOSFETs

LCD / OLED Display Bias

LCD Bias ICs OLED Bias ICs Schottky Diodes

Battery Power Management

USB Power Switches Current Monitors Charger ICs Low-Saturation Bipolar Transistors ZXMP series MOSFETs



Low Dropout Regulators

System Voltage Conversion

Low Dropout Regulators DC-DC Converters Schottky Diodes Low-Saturation Bipolar Transistors

System Interface

USB Power Switches Zener and TVS Arrays

Keypad Backlighting

LED Drivers **Boost Converters** Schottky Diodes

Audio Amplifier

Class D Amplifier



Strong Relationships Drive LCD/LED TV Product Roadmaps

 LCD Display Buffer 40V High-gain BJT

System Power Conversion

Low Dropout Regulators DC-DC Converters Voltage References Synchronous MOSFET Controllers 40V/100V SBR and Schottkys Bridge Rectifier Diodes

LCD LED Backlighting

Current Monitors 400V High-gain NPN BJT 60V/100V High-gain NPN BJT 60V/100V N-channel MOSFETS

CCFL Backlighting
 30V Low On-resistance MOSFETs



Antenna Tuner
 DC-DC Converters
 40V Schottkys

System Interface USB Power Switches Zener and TVS Arrays

System Power Management

Buck DC-DC Converters Low Dropout Regulators 20V/30V/40V SBR® and Schottkys 30V P-Channel MOSFETs 30V Low-saturation PNP BJT

Audio Amplifier

Buck DC-DC Converters Schottky Diodes SBR Class D Amplifier



Product Breadth and Performance for Computing Platforms

LCD / LED Backlighting

LED Drivers Boost Converters Schottky Diodes

System Voltage Conversion

Low Dropout Regulators DC-DC Converters Schottky Diodes Low-Saturation BJT

Battery Power Management

Current Monitors Load Switches Low-Saturation BJT ZXMP series MOSFETs

Open / Close Detection

Hall Effect Sensors Hall Effect Drivers



Audio Amplifier
 Buck DC-DC Converters
 Schottky Diodes
 Super Barrier Rectifiers
 Class D Amplifier

Wireless Connectivity

DC-DC Converters Low Dropout Regulators

System Power Management

Buck DC-DC Converters Low Dropout Regulators Super Barrier Rectifiers Schottky Diodes P-Channel MOSFETs Low-Saturation BJT

System Interface

USB Power Switches Zener and TVS Arrays



Automotive Quality for Demanding Automotive Applications

Body Control Module

Bipolar Transistors Shunt Regulator Voltage Reference IntelliFET MOSFETs Hall Sensor

Powertrain

MOSFET Hall Sensor Super Barrier Rectifier® (SBR)

Daytime Running Lights

LED Drivers Schottky Diodes MOSFETs Bipolar Transistors

SBR and IntelliFET are registered trademarks of Diodes Incorporated

Automotive Networking

ESD Protection
TVS Protection

Interior Light

LED Drivers Schottky Diodes MOSFETs Bipolar Transistors

Seat Control Module

Hall Sensor SBR IntelliFET® Voltage Reference

Braking Control Unit

Voltage Reference IntelliFETs MOSFETs Hall Sensor



Power and Signal Management for the Broad Industrial Market

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Illumination

LED Drivers Synchronous Rectifiers HV Rectifiers and Bridges **SBRs HV Switches**

MOSFETs

System Protection

Hall Sensors **ESD Protection** TVS Protection

Signal Conditioning

Op Amps Comparators Linear Hall Voltage Reference Logic **Current Monitors ESD Protection** TVS Protection



Actuators/Drivers

Hall Sensors Relay Drivers IntelliFET **MOSFETs**

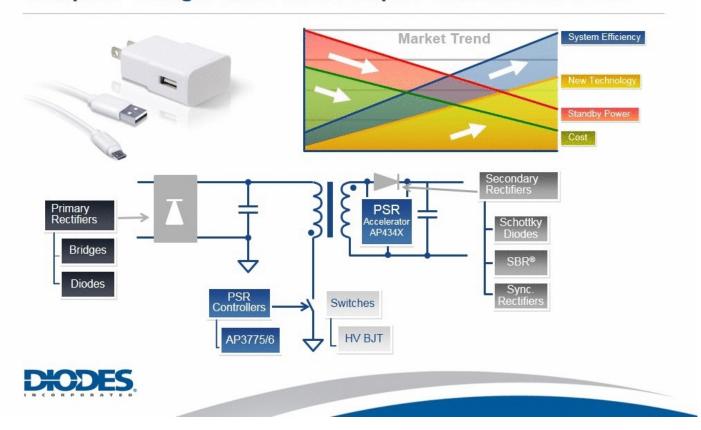
Motor Control

Hall Sensors Motor Control/Drivers **MOSFETs** H-Bridges SBR Gate Drivers

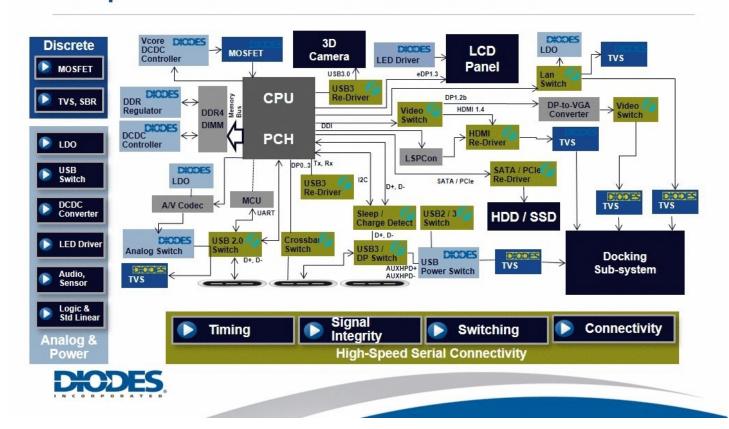
Power Management

AC-DC Converters DC-DC Converters LDO Regulators **HV Regulators** Shunt Regulators Gate Drivers Synchronous Rectifiers **HV Rectifiers and Bridges** SBRs **HV** Switches

Complete Charger and Power Adapter Solution and Trend



Complete Platform Solutions: Notebooks



Packaging Focus: Miniaturization and Power Efficiency





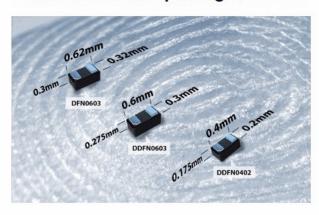
~ 2015

2016 ~

Packaging Focus: Miniaturization and Power Efficiency

Miniaturization

DDFN0402 Possibly the smallest Discrete semiconductor package.



Power Efficiency

Compared to a TO252, the PowerDI®5 package delivers twice the power density from a 55% smaller footprint.





Efficient Manufacturing + Superior Processes

Packaging

- Shanghai-based packaging with capacity approximately 30 billion units
- The new packaging facility in Chengdu has a potential capacity of 3X that of Shanghai
- Additional packaging facilities in Neuhaus, Germany and in Chengdu, China



Wafer Fabs

- Two discrete fabs, two analog fabs in Kansas City, Missouri (5" and 6"), Oldham, United Kingdom (6"), and Shanghai (6") respectively
- Bipolar, BiCMOS, CMOS & BCD process
- Strong engineering capabilities







Collaborative Customer Relationships





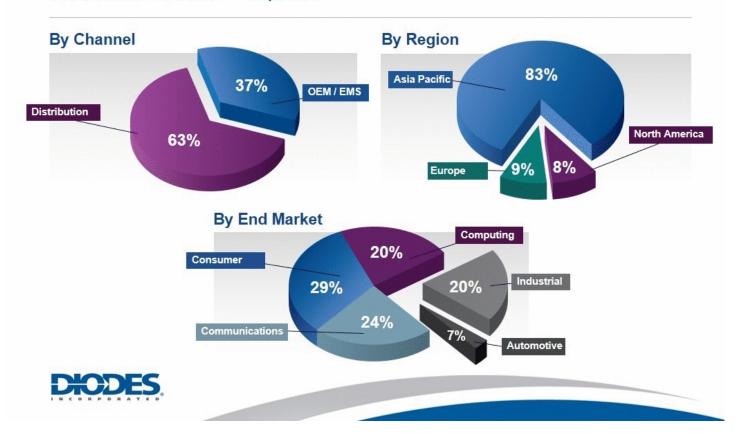
Revenue Growth



* (Acquisition Years)



Revenue Profile - 4Q2016



Summary of Year 2016

- Revenue was \$942.2 million, an increase of 11.0 percent over the \$848.9 million in 2015;
- GAAP gross profit was a record \$286.9 million as compared to \$248.6 million in 2015;
- GAAP gross margin improved 120 base points to 30.5 percent from 29.3 percent in 2015;
- GAAP net income was \$15.9 million, or \$0.32 per diluted share, compared to \$24.3 million, or \$0.49 per diluted share in 2015;
- Non-GAAP adjusted net income was a \$38.4 million, or \$0.77 per diluted share, compared to \$42.3 million, or \$0.86 per diluted share in 2015;
- Excluding \$9.1 million, net of tax, non-cash share-based compensation expense, both GAAP net income and non-GAAP adjusted net income would have increased by \$0.18 per diluted share; and
- Achieved \$124.7 million cash flow from operations and \$66.2 millions free cash flow, including \$58.5 million of capital
 expenditure or 6.2 percent of revenue. Net cash flow was \$29.4 million, which includes the pay down of \$36.4 million
 of long-term debt and \$18 million for the share buyback.



Fourth Quarter 2016 Financial Performance

In millions, except per share	4Q15	3Q16	4Q16	
Revenue	\$214.4	\$250.7	\$232.1	
Revenue Growth	8.3%	-7.4%		
Gross Profit (GAAP)	\$53.6	\$80.6	\$67.3	
Gross Profit Margin % (GAAP)	25.0%	32.2%	29.0%	
Net Income (GAAP)	- \$4.8	\$10.6	\$1.3	
Net Income (non-GAAP)	\$6.7	\$15.1	\$7.7	
EPS (non-GAAP)	\$0.14	\$0.30	\$0.15	
Cash Flow from Operations	\$21.4	\$33.1	\$49.8	
EBITDA (non-GAAP)	\$16.6	\$42.5	\$29.2	



Balance Sheet

In millions	Dec 31, 2014	Dec 31, 2015	Dec 31, 2016
Cash	\$243	\$218	\$248
Short-term Investments	\$12	\$65	\$30
Inventory	\$182	\$203	\$193
Current Assets	\$676	\$751	\$733
Total Assets	\$1179	\$1599	\$1531
Long-term Debt	\$141	\$454	\$413
Total Liabilities	\$369	\$756	\$708
Total Equity	\$810	\$843	\$820



1Q 2017 Business Outlook

- Expect revenue to range between \$220 million and \$240 million, or down 5.2 to up 3.4 percent sequentially, reflecting typical seasonality as well as a one month impact from the KFAB fire;
- Expect gross margin to be 28.5 percent, plus or minus 1 percent;
- Non-GAAP operating expenses, which are GAAP operating expense adjusted for retention costs and amortization of acquisition-related intangible assets, are expected to be approximately 25.0 percent of revenue, plus or minus 1 percent;
- Expect other expense to be approximately \$4.3 million which includes \$1.5 million of KFAB cleanup and repair cost;
- Expect income tax rate to be 29 percent, plus or minus 3 percent, and shares used to calculate diluted EPS for the first quarter are anticipated to be approximately \$50.4 million;
- Purchase accounting adjustments for Pericom and previous acquisitions of \$4.2 million after tax are not included in these non-GAAP estimates.
- Diodes' KFAB facility will cease operations late in the third quarter 2017 with production moved to other Diodes' wafer fabs and external foundries and the premises vacated by November 15, 2017. The pre-tax closure costs are expected to be \$10 million to \$12 million in 2017 with approximately \$1.1 million in first quarter 2017. These shutdown costs have not been included in the above estimates.



Global Manufacturing Infrastructure



Diodes Strategy: Profitable Growth











Thank you

Diodes was named one of the 10 Best Stocks of the Past 20 Years

March 2012

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